

# PBSS304NX,115 Datasheet



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DiGi Electronics Part Number PBSS304NX,115-DG

Manufacturer Nexperia USA Inc.

Manufacturer Product Number PBSS304NX,115

Description TRANS NPN 60V 4.7A SOT89

Detailed Description Bipolar (BJT) Transistor NPN 60 V 4.7 A 130MHz 2.1

W Surface Mount SOT-89



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

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# **Purchase and inquiry**

| Manufacturer Product Number:                 | Manufacturer:                          |
|--|--|
| PBSS304NX,115                                | Nexperia USA Inc.                      |
| Series:                                      | Product Status:                        |
|  | Active                                 |
| Transistor Type:                             | Current - Collector (Ic) (Max):        |
| NPN  | 4.7 A                                  |
| Voltage - Collector Emitter Breakdown (Max): | Vce Saturation (Max) @ lb, lc:         |
| 60 V   | 245mV @ 235mA, 4.7A                    |
| Current - Collector Cutoff (Max):            | DC Current Gain (hFE) (Min) @ Ic, Vce: |
| 100nA (ICBO)                                 | 250 @ 2A, 2V                           |
| Power - Max:                                 | Frequency - Transition:                |
| 2.1 W  | 130MHz                                 |
| Operating Temperature:                       | Grade:                                 |
| 150°C (TJ)                                   | Automotive                             |
| Qualification:                               | Mounting Type:                         |
| AEC-Q100                                     | Surface Mount                          |
| Package / Case:                              | Supplier Device Package:               |
| TO-243AA                                     | SOT-89                                 |
| Base Product Number:                         |  |
| PBSS304                                      |  |

# **Environmental & Export classification**

| RoHS Status:     | Moisture Sensitivity Level (MSL): |
|------------------|-----------------------------------|
| ROHS3 Compliant  | 1 (Unlimited)                     |
| REACH Status:    | ECCN:                             |
| REACH Unaffected | EAR99                             |
| HTSUS:           |                                   |
| 8541.29.0075     |                                   |



**Product data sheet** 

## 1. General description

NPN low  $V_{CEsat}$  transistor in a SOT89 (SC-62/TO-243) small and flat lead Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS304PX

#### 2. Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain (h<sub>FE</sub>) at high I<sub>C</sub>
- · High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- AEC-Q101 qualified

# 3. Applications

- High-voltage DC-to-DC conversion
- · High-voltage MOSFET gate driving
- High-voltage motor control
- · High-voltage power switches (e.g. motors, fans)
- Automotive applications

### 4. Quick reference data

Table 1. Quick reference data

| Symbol             | Parameter                               | Conditions   | Min | Тур | Max | Unit |
|--------------------|---|--|-----|-----|-----|------|
| V <sub>CEO</sub>   | collector-emitter voltage               | open base  | -   | -   | 60  | V    |
| I <sub>C</sub>     | collector current                       |  | -   | -   | 4.7 | Α    |
| I <sub>CM</sub>    | peak collector current                  | single pulse; t <sub>p</sub> ≤ 1 ms  | -   | -   | 9.4 | Α    |
| R <sub>CEsat</sub> | collector-emitter saturation resistance | $I_C$ = 4 A; $I_B$ = 200 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C | -   | 37  | 53  | mΩ   |



60 V, 4.7 A NPN low VCEsat transistor

# 5. Pinning information

#### **Table 2. Pinning information**

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|--------------------|----------------|
| 1   | E      | emitter     |                    | С              |
| 2   | С      | collector   |                    |                |
| 3   | В      | base        | 3 2 1              | В — ,<br>Е     |
|     |        |             | SOT89              | sym123         |

# 6. Ordering information

#### **Table 3. Ordering information**

| Type number | Package | Package  |         |  |  |  |
|-------------|---------|--|---------|--|--|--|
|             | Name    | Description  | Version |  |  |  |
| PBSS304NX   |         | plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body | SOT89   |  |  |  |

# 7. Marking

#### Table 4. Marking codes

| Type number | Marking code[1] |
|-------------|-----------------|
| PBSS304NX   | %5E             |

[1] % = placeholder for manufacturing site code

# 8. Limiting values

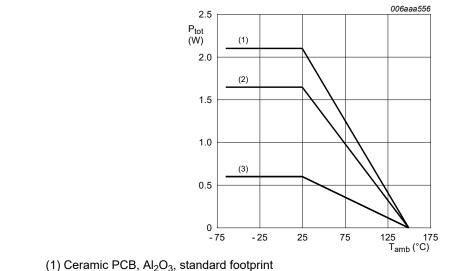
#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter                 | Conditions                          |     | Min | Max  | Unit |
|------------------|---------------------------|-------------------------------------|-----|-----|------|------|
| V <sub>CBO</sub> | collector-base voltage    | open emitter                        |     | -   | 60   | V    |
| V <sub>CEO</sub> | collector-emitter voltage | open base                           |     | -   | 60   | V    |
| V <sub>EBO</sub> | emitter-base voltage      | open collector                      |     | -   | 5    | V    |
| I <sub>C</sub>   | collector current         |                                     |     | -   | 4.7  | Α    |
| I <sub>CM</sub>  | peak collector current    | single pulse; t <sub>p</sub> ≤ 1 ms |     | -   | 9.4  | Α    |
| P <sub>tot</sub> | total power dissipation   | T <sub>amb</sub> ≤ 25 °C            | [1] | -   | 0.6  | W    |
|                  |                           |                                     | [2] | -   | 1.65 | W    |
|                  |                           |                                     | [3] | -   | 2.1  | W    |
| Tj               | junction temperature      |                                     |     | -   | 150  | °C   |
| T <sub>amb</sub> | ambient temperature       |                                     |     | -65 | 150  | °C   |
| T <sub>stg</sub> | storage temperature       |                                     |     | -65 | 150  | °C   |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- 3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

#### 60 V, 4.7 A NPN low VCEsat transistor



- (2) FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>
- (3) FR4 PCB, standard footprint

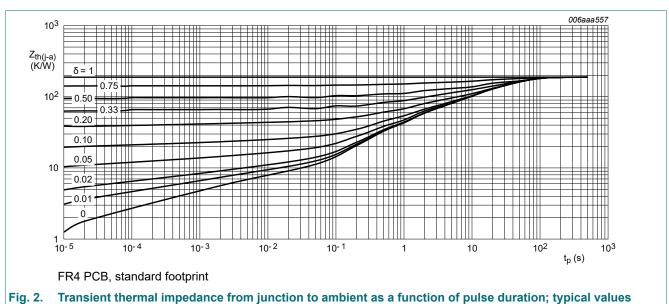
**Power derating curves** Fig. 1.

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

| Symbol                | Parameter  | Conditions  |     | Min | Тур | Max | Unit |
|-----------------------|--|-------------|-----|-----|-----|-----|------|
| $R_{th(j-a)}$         | thermal resistance from                          | in free air | [1] | -   | -   | 208 | K/W  |
|                       | junction to ambient                              |             | [2] | -   | -   | 76  | K/W  |
|                       |  |             | [3] | -   | -   | 60  | K/W  |
| R <sub>th(j-sp)</sub> | thermal resistance from junction to solder point |             |     | -   | -   | 20  | K/W  |

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint. [3]



#### 60 V, 4.7 A NPN low VCEsat transistor

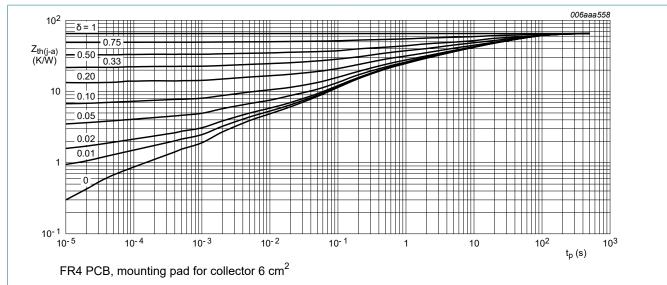
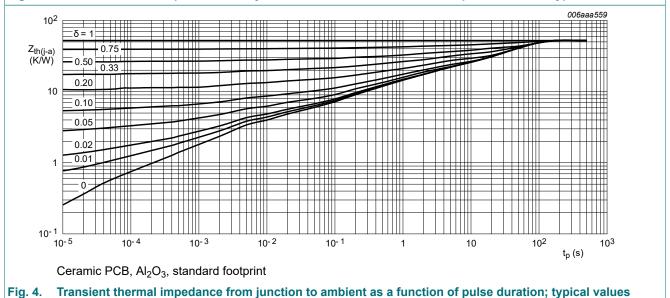


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



#### 10. Characteristics

#### **Table 7. Characteristics**

| Symbol           | Parameter                    | Conditions  | Min | Тур | Max | Unit |
|------------------|------------------------------|---|-----|-----|-----|------|
| I <sub>CBO</sub> |                              | $V_{CB} = 60 \text{ V}; I_{E} = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$ | -   | -   | 100 | nA   |
|                  | current                      | $V_{CB} = 60 \text{ V}; I_E = 0 \text{ A}; T_j = 150 \text{ °C}$            | -   | -   | 50  | μΑ   |
| I <sub>EBO</sub> | emitter-base cut-off current | V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C       | -   | -   | 100 | nA   |

### 60 V, 4.7 A NPN low VCEsat transistor

| Symbol             | Parameter                               | Conditions  | Min | Тур  | Max  | Unit |
|--------------------|---|---|-----|------|------|------|
|                    |   | $V_{CE}$ = 2 V; $I_{C}$ = 0.5 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                          | 300 | 520  | -    |      |
|                    |   | $V_{CE}$ = 2 V; $I_{C}$ = 1 A; pulsed; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C                     | 300 | 500  | -    |      |
|                    |   | $V_{CE}$ = 2 V; $I_{C}$ = 2 A; pulsed; $t_{p} \le 300 \ \mu s$ ;<br>δ ≤ 0.02; $T_{amb}$ = 25 °C                 | 250 | 470  | -    |      |
|                    |   | $V_{CE}$ = 2 V; $I_{C}$ = 4 A; pulsed; $t_{p} \le 300 \ \mu s$ ;<br>δ ≤ 0.02; $T_{amb}$ = 25 °C                 | 150 | 250  | -    |      |
|                    |   | $V_{CE}$ = 2 V; $I_{C}$ = 6 A; pulsed; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C                     | 75  | 115  | -    |      |
| V <sub>CEsat</sub> | collector-emitter saturation voltage    | $I_C$ = 0.5 A; $I_B$ = 50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                             | -   | 25   | 35   | mV   |
|                    |   | $I_C$ = 1 A; $I_B$ = 50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                               | -   | 50   | 70   | mV   |
|                    |   | $I_C$ = 1 A; $I_B$ = 10 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                               | -   | 85   | 120  | mV   |
|                    |   | $I_C$ = 2 A; $I_B$ = 40 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                                 | -   | 105  | 150  | mV   |
|                    |   | $I_C$ = 4 A; $I_B$ = 200 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                                | -   | 145  | 210  | mV   |
|                    |   | $I_C$ = 4 A; $I_B$ = 400 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                                | -   | 140  | 200  | mV   |
|                    |   | $I_C$ = 4 A; $I_B$ = 80 mA; pulsed; $t_p \le$ 300 µs; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C                     | -   | 190  | 290  | mV   |
|                    |   | $I_C$ = 4.7 A; $I_B$ = 235 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                            | -   | 170  | 245  | mV   |
| R <sub>CEsat</sub> | collector-emitter saturation resistance | $I_C$ = 4 A; $I_B$ = 200 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                                | -   | 37   | 53   | mΩ   |
|                    |   | $I_C$ = 4 A; $I_B$ = 80 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                                 | -   | 48   | 73   | mΩ   |
| V <sub>BEsat</sub> | base-emitter saturation voltage         | $I_C$ = 1 A; $I_B$ = 100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                              | -   | 0.82 | 0.9  | V    |
|                    |   | $I_C$ = 4 A; $I_B$ = 400 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                              | -   | 0.94 | 1.05 | V    |
| $V_{BEon}$         | base-emitter turn-on voltage            | $V_{CE}$ = 2 V; $I_{C}$ = 2 A; pulsed; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C                     | -   | 0.75 | 0.85 | V    |
| t <sub>d</sub>     | delay time                              | $V_{CC} = 12.5 \text{ V}; I_C = 3 \text{ A}; I_{Bon} = 0.15 \text{ A};$   | -   | 15   | -    | ns   |
| t <sub>r</sub>     | rise time                               | I <sub>Boff</sub> = -0.15 A; T <sub>amb</sub> = 25 °C   | -   | 95   | -    | ns   |
| t <sub>on</sub>    | turn-on time                            |   | -   | 110  | -    | ns   |
| t <sub>s</sub>     | storage time                            |   | -   | 360  | -    | ns   |
| t <sub>f</sub>     | fall time                               |   | -   | 195  | -    | ns   |
| t <sub>off</sub>   | turn-off time                           |   | -   | 555  | -    | ns   |
| f <sub>T</sub>     | transition frequency                    | $V_{CE}$ = 10 V; $I_{C}$ = 100 mA; f = 100 MHz; $T_{amb}$ = 25 °C   | -   | 130  | -    | MHz  |
| C <sub>c</sub>     | collector capacitance                   | $V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; $<br>$T_{amb} = 25 \text{ °C}$ | -   | 48   | 70   | pF   |

#### 60 V, 4.7 A NPN low VCEsat transistor

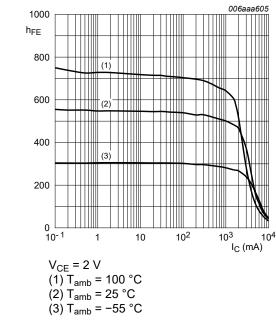


Fig. 5. DC current gain as a function of collector current; typical values

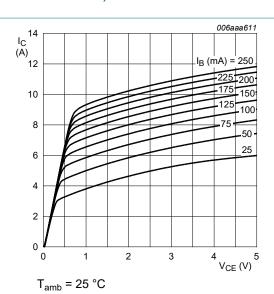
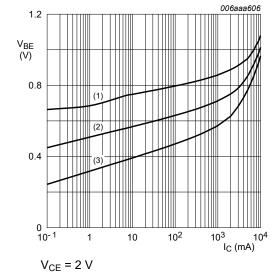


Fig. 6. Collector current as a function of collectoremitter voltage; typical values

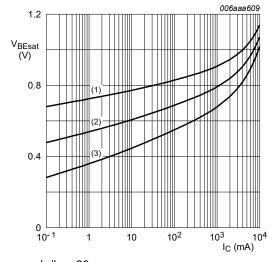


(1)  $T_{amb} = -55$  °C

(2) T<sub>amb</sub> = 25 °C

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig. 7. Base-emitter voltage as a function of collector current; typical values



 $I_C/I_B = 20$ 

(1)  $T_{amb} = -55$  °C

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

#### 60 V, 4.7 A NPN low VCEsat transistor

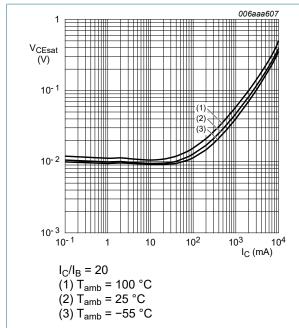


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

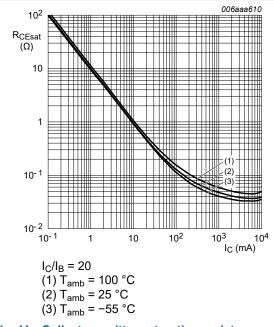


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

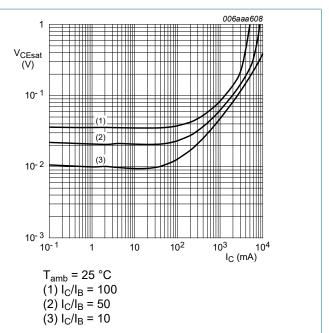


Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values

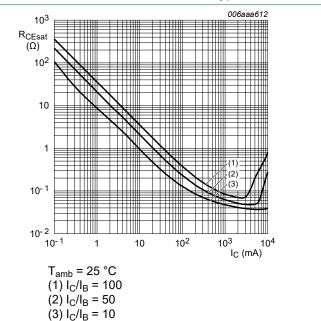
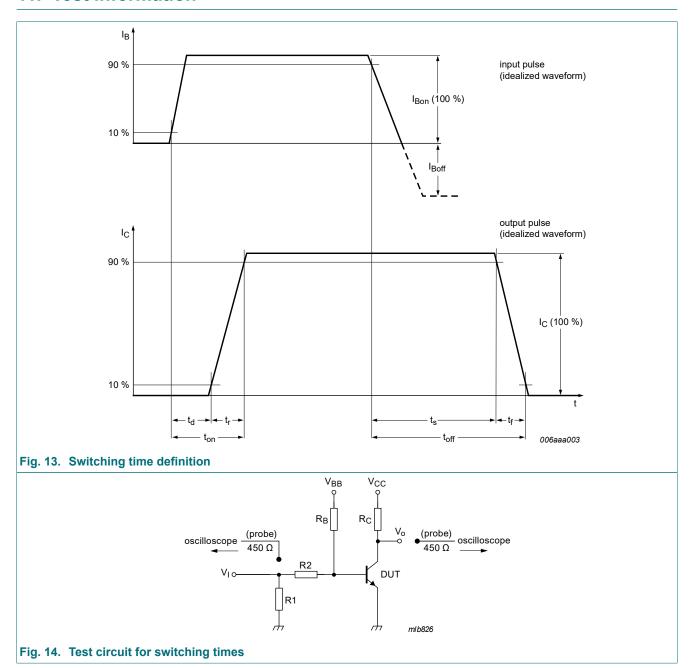


Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values

60 V, 4.7 A NPN low VCEsat transistor

# 11. Test information

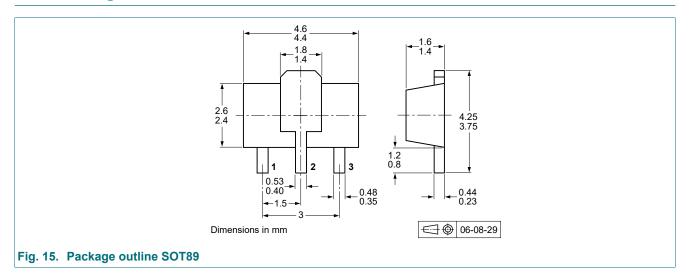


#### **Quality information**

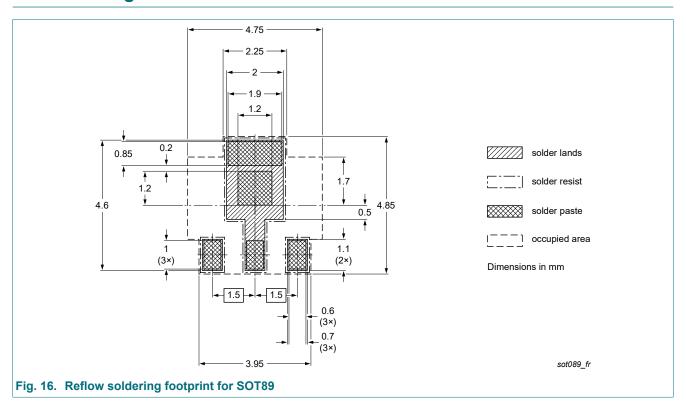
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

60 V, 4.7 A NPN low VCEsat transistor

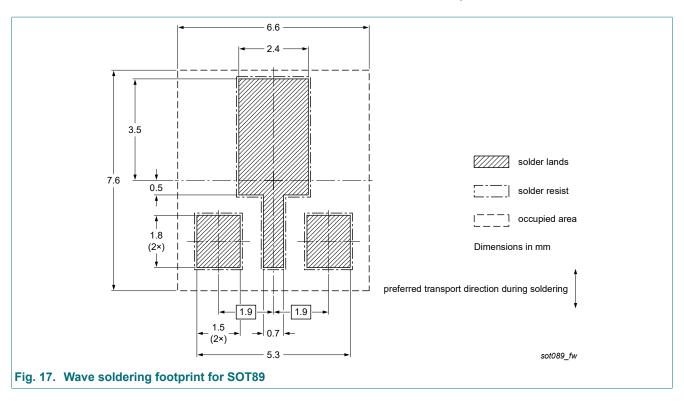
# 12. Package outline



# 13. Soldering



#### 60 V, 4.7 A NPN low VCEsat transistor



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PBSS304NX

60 V, 4.7 A NPN low VCEsat transistor

# 14. Revision history

## Table 8. Revision history

| table of Novicion microry |   |                    |               |             |  |
|---------------------------|---|--------------------|---------------|-------------|--|
| Data sheet ID             | Release date  | Data sheet status  | Change notice | Supersedes  |  |
| PBSS304NX v.3             | 20231109  | Product data sheet | -             | PBSS304NX_2 |  |
| Modifications:            | <ul> <li>The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> <li>Section "Packing information" removed.</li> </ul> |                    |               |             |  |
| PBSS304NX_2               | 20091120  | Product data sheet | -             | PBSS304NX_1 |  |
| PBSS304NX_1               | 20060816  | Product data sheet | -             | -           |  |

#### 60 V, 4.7 A NPN low VCEsat transistor

# 15. Legal information

#### **Data sheet status**

| Document status [1][2]         | Product<br>status [3] | Definition  |
|--------------------------------|-----------------------|---|
| Objective [short] data sheet   | Development           | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification         | This document contains data from the preliminary specification.                       |
| Product [short]<br>data sheet  | Production            | This document contains the product specification.                                     |

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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# Nexperia

# PBSS304NX

#### 60 V, 4.7 A NPN low VCEsat transistor

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| -                       | Features and benefits |

For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 9 November 2023

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Tel: +00 852-30501935